# 2SD2185G

## Silicon NPN epitaxial planar type

For low-frequency output amplification Complementary to 2SB1440G

#### ■ Features

- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

### ■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter                             | Symbol         | Rating      | Unit |  |
|---------------------------------------|----------------|-------------|------|--|
| Collector-base voltage (Emitter open) | $V_{CBO}$      | 50          | V    |  |
| Collector-emitter voltage (Base open) | $V_{CEO}$      | 50          | V    |  |
| Emitter-base voltage (Collector open) | $V_{EBO}$      | 5           | V    |  |
| Collector current                     | $I_{\rm C}$    | 3           | A    |  |
| Peak collector current                | $I_{CP}$       | 4           | A    |  |
| Collector power dissipation *         | P <sub>C</sub> | 1           | W    |  |
| Junction temperature                  | Tj             | 150         | °C   |  |
| Storage temperature                   | $T_{stg}$      | -55 to +150 | °C   |  |

Note) \*: Printed circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion

#### ■ Package

- Code MiniP3-F2
- Pin Name
  - 1: Base
  - 2: Collector
  - 3: Emitter
- Marking Symbol: 1H

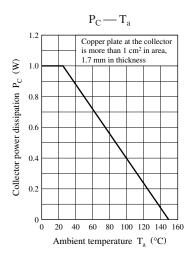
### ■ Electrical Characteristics T<sub>a</sub> = 25°C ± 3°C

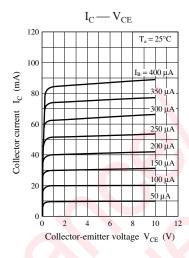
| Parameter                                    | Symbol               | Conditions   | Min | Тур  | Max  | Unit |
|--|----------------------|--|-----|------|------|------|
| Collector-base voltage (Emitter open)        | $V_{CBO}$            | $I_C = 10  \mu A, I_E = 0$   | 50  |      |      | V    |
| Collector-emitter voltage (Base open)        | V <sub>CEO</sub>     | $I_C = 1 \text{ mA}, I_B = 0$                                      | 50  |      |      | V    |
| Emitter-base voltage (Collector open)        | V <sub>EBO</sub>     | $I_E = 10 \ \mu A, I_C = 0$  | 5   |      |      | V    |
| Collector-base cutoff current (Emitter open) | I <sub>CBO</sub>     | $V_{CB} = 20 \text{ V}, I_{E} = 0$                                 |     |      | 0.1  | μΑ   |
| Forward current transfer ratio               | h <sub>FE1</sub> *   | $V_{CE} = 2 \text{ V}, I_{C} = 200 \text{ mA}$                     | 120 |      | 340  |      |
|  | h <sub>FE2</sub>     | $V_{CE} = 2 \text{ V}, I_{C} = 1.0 \text{ A}$                      | 80  |      |      |      |
| Collector-emitter saturation voltage         | V <sub>CE(sat)</sub> | $I_C = 1 \text{ A}, I_B = 50 \text{ mA}$                           |     | 0.15 | 0.30 | V    |
| Base-emitter saturation voltage              | V <sub>BE(sat)</sub> | $I_C = 1 \text{ A}, I_B = 50 \text{ mA}$                           |     | 0.85 | 1.20 | V    |
| Transition frequency                         | $f_T$                | $V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$ |     | 120  |      | MHz  |
| Collector output capacitance                 | C <sub>ob</sub>      | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$                |     | 20   | 35   | pF   |
| (Common base, input open circuited)          |                      |  |     |      |      |      |

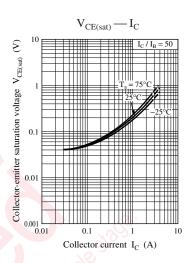
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

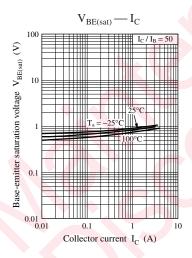
#### 2. \*: Rank classification

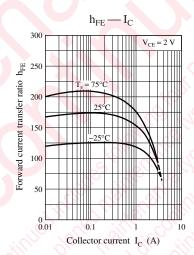
| Rank      | R          | S          |
|-----------|------------|------------|
| $h_{FE1}$ | 120 to 240 | 170 to 340 |

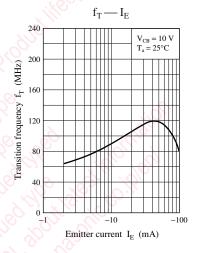


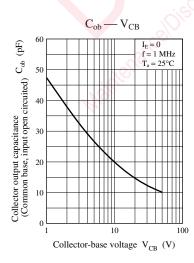




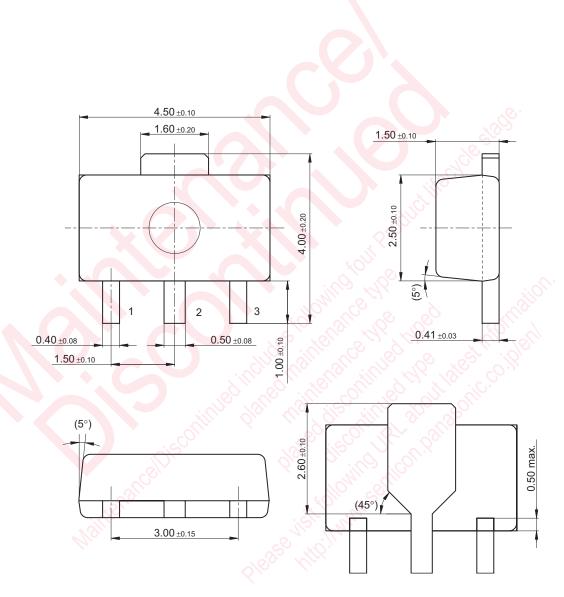








MiniP3-F2 Unit: mm



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